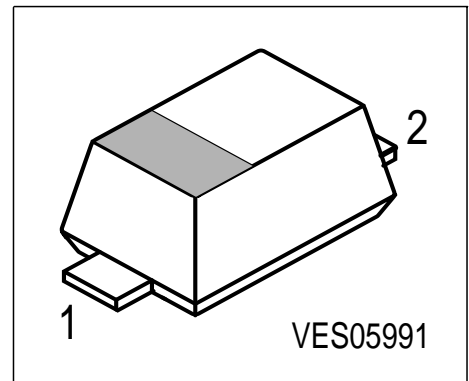


Silicon Tuning Diode

Preliminary data

- Excellent linearity
- High Q hyperabrupt tuning diode
- Low series inductance
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- For low frequency control elements such as TCXOs and VCXOs
- Very low capacitance spread



Type	Marking	Ordering Code	Pin Configuration		Package
BBY 58-02W	8	Q62702-B916	1 = C	2 = A	SCD-80

Maximum Ratings

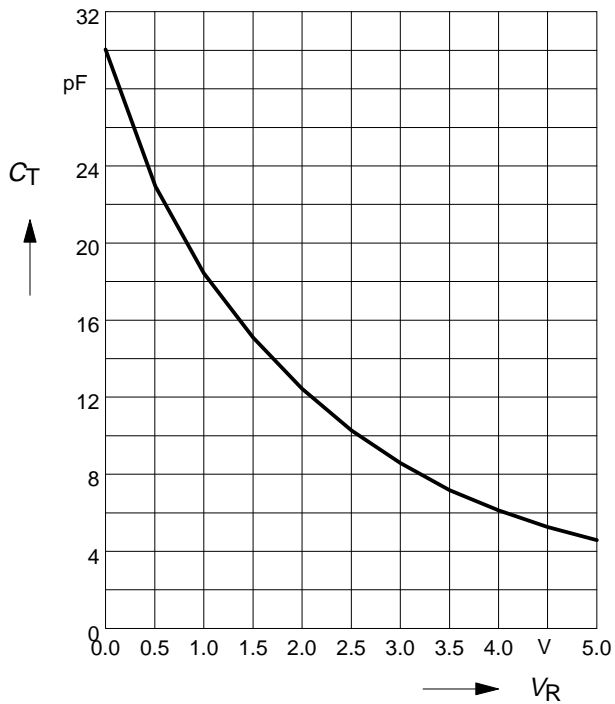
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ...+150	°C
Storage temperature	T_{stg}	-55 ...+150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

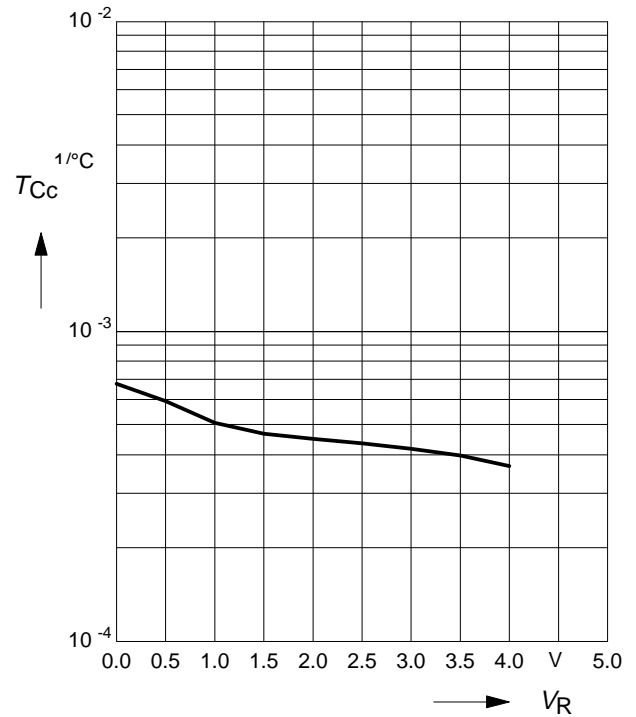
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current $V_R = 8\text{ V}$	I_R	-	-	1	nA
Reverse current $V_R = 8\text{ V}, T_A = 65^\circ\text{C}$	I_R	-	-	100	
AC characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 3\text{ V}, f = 1\text{ MHz}$ $V_R = 4\text{ V}, f = 1\text{ MHz}$	C_T	17.5 - - 5.5	18.3 12.35 8.6 6	19.3 - - 6.6	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 3\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T3}	-	2.15	-	-
Capacitance ratio $V_R = 1\text{ V}, V_R = 4\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T4}	2.8	3.05	3.3	
Series resistance $V_R = 1\text{ V}, f = 470\text{ MHz}$	r_s	-	0.25	-	Ω
Case capacitance $f = 1\text{ MHz}$	C_C	-	0.09	-	pF
Series inductance chip to ground	L_s	-	0.6	-	nH

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$



Normalized diode capacitance

$$C_{(T_A)} / C_{(25^\circ\text{C})} = f(T_A)$$

$f = 1\text{MHz}, V_R = \text{Parameter}$

